General purpose transistor (isolated transistor and diode)

EML11 / UML11N

2SA1774 and a RB521S-30 are housed independently in a EMT5 or UMT5 package.

●Applications

DC / DC converter
Motor driver

●Features

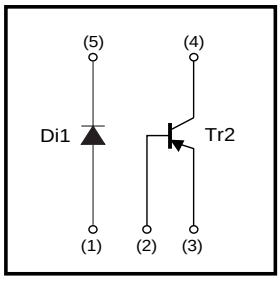
1) Tr2: Small Signal Transistor
   Di1: Low V_F
2) Small package

●Structure

Silicon epitaxial planar transistor
Schottky barrier diode

The following characteristics apply to both Di1 and Tr2.

●Equivalent circuit (EML11 / UML11N)

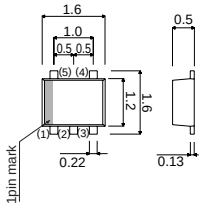


●Packaging specifications

Type	EML11	UML11N
Package	EMT5	UMT5
Marking	L11	L11
Code	T2R	TR
Basic ordering unit(pieces)	8000	3000

●External dimensions (Unit : mm)

EMT5

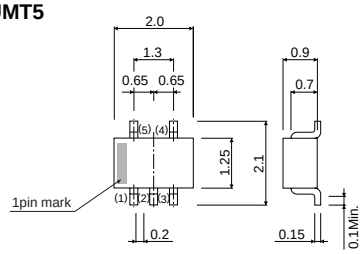


Each lead has same dimensions

Abbreviated symbol : L11

ROHM : EMT5

UMT5



Each lead has same dimensions

Abbreviated symbol : L11

ROHM : UMT5
EIAJ : SC-88A

●**Absolute maximum ratings** (Ta=25°C)

Di1

Parameter	Symbol	Limits	Unit
Average rectified forward current	I_O	200	mA
Forward current surge peak (60Hz, 1∞)	I_{FSM}	1	A
Reverse voltage (DC)	V_R	30	V
Junction temperature	Tj	125	°C

Tr2

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	–60	V
Collector-emitter voltage	V_{CEO}	–50	V
Emitter-base voltage	V_{EBO}	–6	V
Collector current	I_C	–150	mA
Power dissipation	P_D	120	mW *
Junction temperature	Tj	150	°C

∗ Each terminal mounted on a recommended.

Di1 / DTr2

Parameter	Symbol	Limits	Unit
Power dissipation	P_d	150	mW *
Storage temperature	Tstg	–55 to +125	°C

∗ Each terminal mounted on a recommended.

●**Electrical characteristics** (Ta=25°C)

Di1

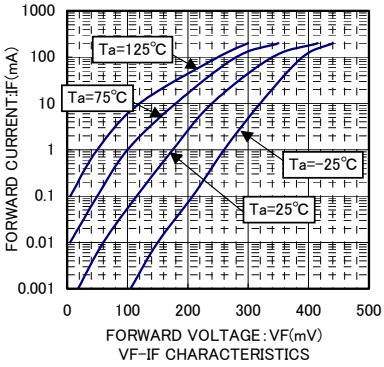
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	–	0.40	0.50	V	I_F=200mA
Reverse current	I_R	–	4.0	30	μA	V_R=10V

Tr2

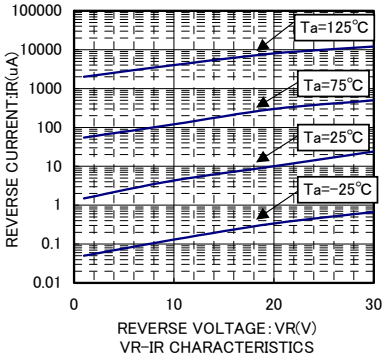
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	–60	–	–	V	I_C=–50μA
Collector-emitter breakdown voltage	BV_{CEO}	–50	–	–	V	I_C=–1mA
Emitter-base breakdown voltage	BV_{EBO}	–6	–	–	V	I_E=–50μA
Collector cutoff current	I_{CBO}	–	–	–100	nA	V_{CB}=–60V
Emitter cutoff current	I_{EBO}	–	–	–100	nA	V_{EB}=–6V
Collector-emitter saturation voltage	$V_{CE(sat)}$	–	–	–500	mV	I_C/I_B=–50mA/–5mA
DC current transfer ratio	h_{FE}	180	–	390	–	V_{CE}=–6V, I_C=–1mA
Transition frequency	f_T	–	140	–	MHz	V_{CE}=–12V, I_E=2mA, f=100MHz
Output capacitance	Cob	–	4.0	5.0	pF	V_{CB}=–12V, I_E=0A, f=1MHz

●**Electrical characteristic curves**

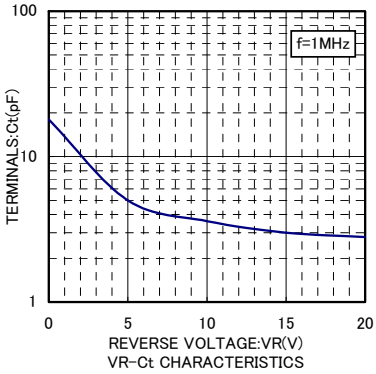
Di1



VF-IF CHARACTERISTICS



VR-IR CHARACTERISTICS



VR-Ct CHARACTERISTICS

Tr2

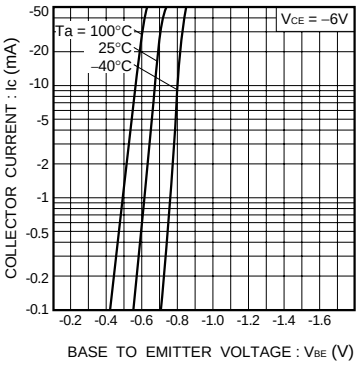


Fig.1 Grounded emitter propagation characteristics

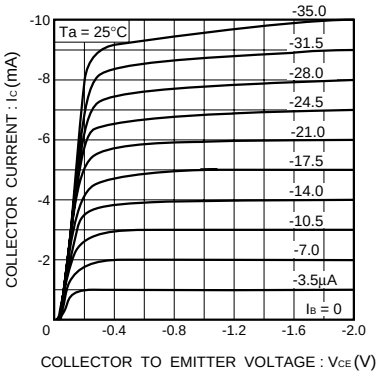


Fig.2 Grounded emitter output characteristics (I)

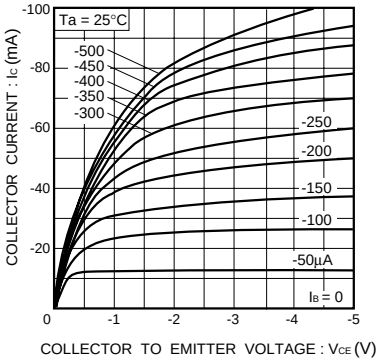


Fig.3 Grounded emitter output characteristics (II)

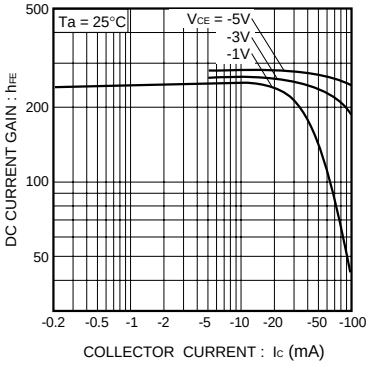


Fig.4 DC current gain vs. collector current (I)

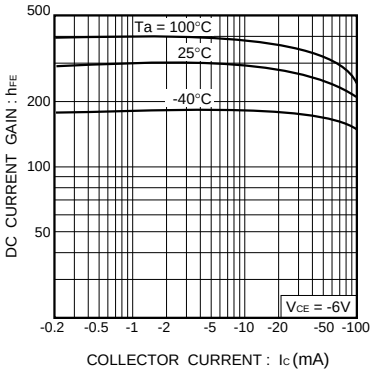


Fig.5 DC current gain vs. collector current (II)

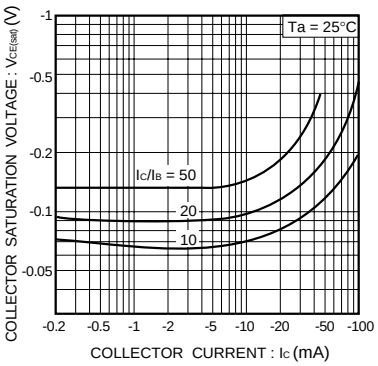


Fig.6 Collector-emitter saturation voltage vs. collector current (I)

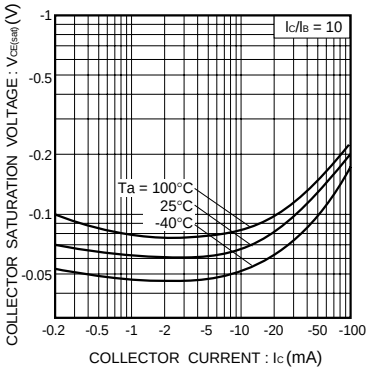


Fig.7 Collector-emitter saturation voltage vs. collector current (II)

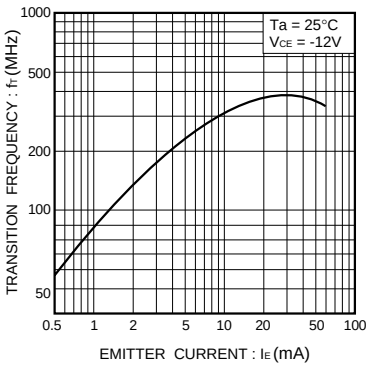


Fig.8 Gain bandwidth product vs. emitter current

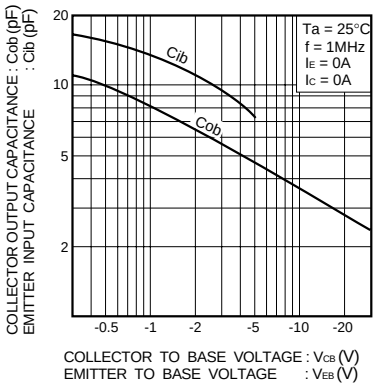


Fig.9 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

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